

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
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TYPE : 6PT2203N3T**

CHIP SIZE	0.4 * 0.4 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	95,200 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	30	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	0.5	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±10	uA	VGS=±20V VDS=0V
2	IDSS			1	uA	VDS=30V VGS=0V
3	BVDSS	32			V	ID=10uA
4	VTH	1		1.6	V	ID=250uA VDS=VGS
5	RDS(on)1		1.0	2.0	Ω	ID=100mA VGS=2.5V
6	RDS(on)2		0.5	1.5	Ω	ID=100mA VGS=4V
7	VSD	0.5		1.1	V	I=100mA VGS=0V

※ Built-in ZD between Gate and Source.

TENTATIVE

NOTE: